IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A semiconductor device comprising:

a semiconductor element;

a lead frame having a first surface on which said semiconductor element is mounted, and a second surface opposite to said first surface;

a metal block on said second surface of said lead frame;

an insulation layer on said metal block opposite said lead frame; [[and]]

a bonding material between said second surface of said lead frame and said metal

block[[,]]; and

a resin package configured to seal said semiconductor element, said lead frame and said metal block while uncovering said insulation layer,

wherein said bonding material has a higher heat conduction than said insulation layer, and

wherein said insulation layer has a higher heat conduction than said resin package.

Claim 2 (Original): The semiconductor device according to claim 1, wherein said metal block is disposed in opposed relation to said semiconductor element.

Claim 3 (Previously Presented): The semiconductor device according to claim 1, wherein said metal block has a wider surface opposite said bonding material than said bonding material.

Claim 4 (Currently Amended): The semiconductor device according to claim 1, A semiconductor device comprising:

a semiconductor element;

a lead frame having a first surface on which said semiconductor element is mounted, and a second surface opposite to said first surface;

a metal block on said second surface of said lead frame;

an insulation layer on said metal block opposite said lead frame; and

a bonding material between said second surface of said lead frame and said metal

block,

wherein said bonding material has a higher heat conduction than said insulation layer, wherein said semiconductor element includes a plurality of semiconductor elements, and

wherein said metal block is separate for each insulated unit between said semiconductor elements, and is provided in corresponding relation to at least one of said semiconductor elements.

Claim 5 (Canceled).

Claim 6 (Currently Amended): The semiconductor device according to claim [[5]] 1, wherein said insulation layer comprises a base material with a same base as said resin package, and ceramic powder.

Claim 7 (Previously Presented): The semiconductor device according to claim 1,

wherein said metal block has a first surface and a second surface opposite said insulation layer,

wherein said first surface of said metal block is closer, as viewed in a vertical direction, to said lead frame than is said second surface of said metal block, and

wherein said bonding material lies between said second surface of said lead frame and said first surface of said metal block.

Claim 8 (Currently Amended): The semiconductor device according to claim 1, A semiconductor device comprising:

a semiconductor element;

a lead frame having a first surface on which said semiconductor element is mounted, and a second surface opposite to said first surface;

a metal block on said second surface of said lead frame;

an insulation layer on said metal block opposite said lead frame; and

a bonding material between said second surface of said lead frame and said metal

block,

wherein said bonding material has a higher heat conduction than said insulation layer,
wherein said lead frame has a third surface on the same side as said second surface,
wherein said third surface is closer, as viewed in a vertical direction, to said
semiconductor element than is said second surface, and

wherein an insulation space is defined between said metal block and said third surface.

Claims 9-11 (Canceled)